
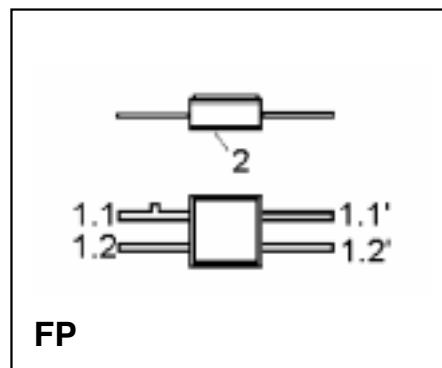


HiRel Silicon PIN Diode

BXY 43P

Features

- **HiRel Discrete and Microwave Semiconductor**
- Current controlled RF resistor for RF attenuators and switches
- High reverse voltage
- Matched diode - pair
- Hermetically sealed microwave package
-  qualified
- ESA/SCC Detail Spec. No.: 5513/030



ESD: Electrostatic discharge sensitive device, observe handling precautions!

Type	Marking	Ordering Code	Pin Configuration	Package
BXY 43P-FP (ql)	-	see below		FP

(ql) Quality Level: P: Professional Quality, Ordering Code: Q62702X164
 H: High Rel Quality, Ordering Code: on request
 S: Space Quality, Ordering Code: on request
 ES: ESA Space Quality, Ordering Code: Q62702X167

(see **Chapter Order Instructions** for ordering example)

Table 1 Maximum Ratings

Parameter	Symbol	Limit Values	Unit
Reverse voltage	V_R	150	V
Forward current	I_F	400	mA
Power dissipation	P_{tot}	500	mW
Operating temperature range	T_{op}	- 55 to + 150	°C
Storage temperature range	T_{stg}	- 65 to + 175	°C
Soldering temperature	T_{sol}	+ 235	°C
Junction temperature	T_j	175	°C
Thermal resistance junction-case	$R_{th(j-c)}$	100	K/W

Electrical Characteristics

Table 2 DC Characteristics at $T_A = 25\text{ °C}$ unless otherwise specified

Parameter	Symbol	Limit Values			Unit
		min.	typ.	max.	
Reverse current 1 $V_{R1} = 150\text{ V}$	I_{R1}	–	–	100	nA
Reverse current 2 $V_{R2} = 100\text{ V}$	I_{R2}	–	–	10	nA
Forward voltage $I_F = 100\text{ mA}$	V_F	–	0.97	1	V

Table 3 AC Characteristics at $T_A = 25\text{ °C}$ unless otherwise specified

Parameter	Symbol	Limit Values			Unit
		min.	typ.	max.	
Total capacitance $V_R = 50\text{ V}, f = 1\text{ MHz}$	C_T	0.4	0.6	0.85	pF
Forward resistance $f = 100\text{ MHz}, I_{F1} = 20\text{ }\mu\text{A}$	R_{F1}	–	55	70	Ω
Forward resistance $f = 100\text{ MHz}, I_{F2} = 1\text{ mA}$	R_{F2}	–	2.2	3.0	Ω
Forward resistance $f = 100\text{ MHz}, I_{F3} = 10\text{ mA}$	R_{F3}	–	0.9	1.5	Ω
Minority carrier lifetime $I_F = 10\text{ mA}, I_R = 6\text{ mA}, I_R = 3\text{ mA}$	τ_L	250	650	–	ns

Table 4 Matching Requirements at $T_A = 25\text{ °C}$ unless otherwise specified

Parameter	Symbol	Limit Values			Unit
		min.	typ.	max.	
Difference in forward resistance 2 ¹⁾	R_{F2}	–	–	15	%
Difference in forward resistance 3 ¹⁾	R_{F3}	–	–	15	%

¹⁾ $\Delta R_F [\%] = 100 \times (RF_Diode2 - RF_Diode1)/RF_Diode1$

Order Instructions

Full type variant including package variant and quality level must be specified by the orderer. For HiRel Discrete and Microwave Semiconductors the ordering code specifies device family and quality level only.

Ordering Form:

Ordering Code: Q...
BXY43P-(x) (ql)
(x): Package Variant
(ql): Quality Level

Ordering Example:

Ordering Code: Q62702X167
BXY43P-FP ES
For BXY43P in Flatpack Package; ESA Space Quality Level

Further Information

See our WWW-Pages:

- Discrete and RF-Semiconductors (Small Signal Semiconductors)
www.siemens.de/semiconductor/products/35/35.htm
- HiRel Discrete and Microwave Semiconductors
www.siemens.de/semiconductor/products/35/353.htm

Please contact also our marketing division:

Tel.: ++89 6362 4480

Fax.: ++89 6362 5568

e-mail: martin.wimmers@hl.siemens.de

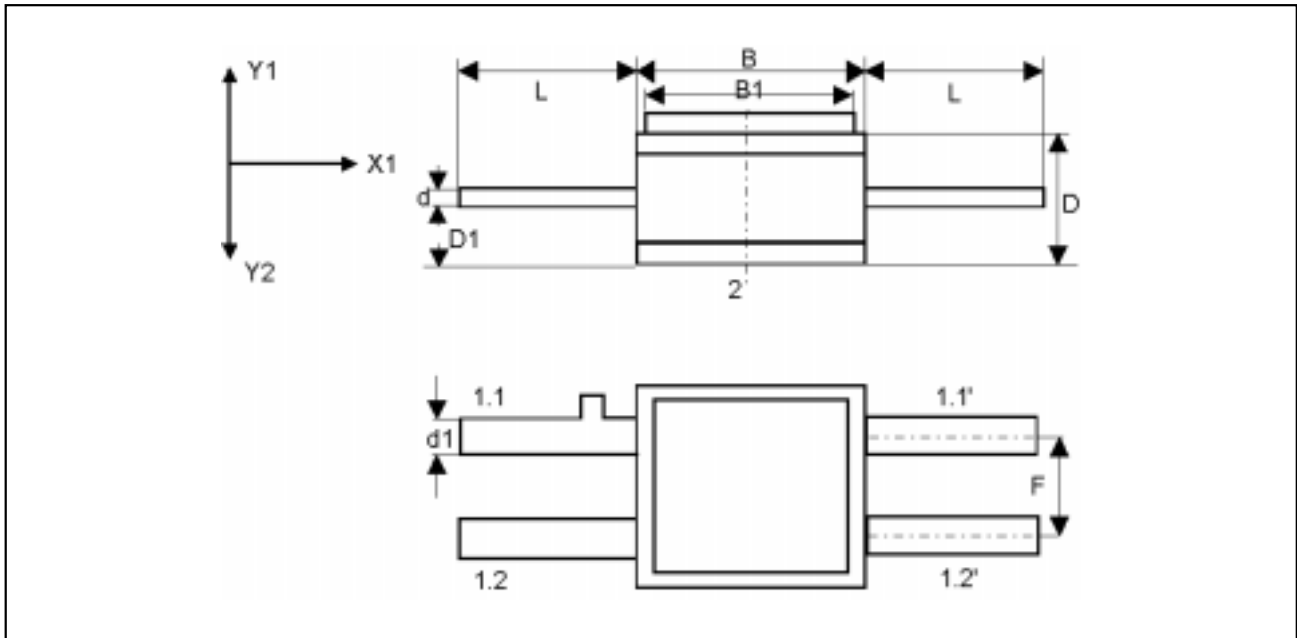


Figure 1 FP Package

Symbol	Millimetre	
	min.	max.
B	3.10	3.55
B1	3.00	3.30
D	1.30	1.70
D1	0.55	0.65
d	0.10	0.15
d1	0.25	0.40
F	2.40	2.60
L	5.50	-